



INTEGRATED RELAY AND INDUCTIVE LOAD DRIVER

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	1.8Ω @ V _{GS} = 5V	630mA
600	$2.4\Omega @ V_{GS} = 3V$	OSUITA

Description and Applications

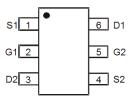
DIODES™ DMN61D8LVTQ provides a single component solution for switching inductive loads such as relays, solenoids, and small DC motors in automotive applications, without the need of a freewheeling diode. DMN61D8LVTQ accepts logic level inputs, thus allowing it to be driven by logic gates, inverters and microcontrollers. It is ideally suited for door, window and antenna relay coils.











Top View

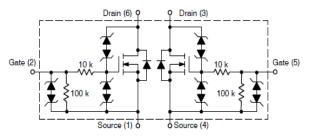
Features and Benefits

- Provides a reliable and robust interface between sensitive logic and DC relay coils
- Replaces 3 to 4 discrete components enabling PCB footprint to be reduced
- Internal active clamp removes the need for external zener diode
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN61D8LVTQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: TSOT26
- Package Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 63
- Weight: 0.013 grams (Approximate)



Equivalent Circuit

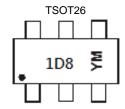
Ordering Information (Note 4)

Part Number	Package	Packing			
Part Number	Fackage	Qty.	Carrier		
DMN61D8LVTQ-7	TSOT26	3,000	Tape & Reel		
DMN61D8LVTQ-13	TSOT26	10,000	Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



1D8 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: J = 2022) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	С		J	K	L	М	N	0	Р	R	S	T
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±12	V		
Continuous Drain Current (Note 6)	Steady $T_A = +25$ °C $T_A = +70$ °C		lo	630 500	mA
Maximum Continuous Body Diode Forward Current	t (Note 6)	Is	0.5	Α	
Single Pulse Drain-to-Source Avalanche Energy (For Relay's Coils/Inductive Loads of 80Ω or Highe	EZ	200	mJ		
Peak Power Dissipation, Drain-to-Source (Non repulse 1.0ms duration) (T _J Initial = +85°C)	` .		PPK	20	W
	p Pulse, Drain-to-Source, R _{SOURCE} = 0.5Ω, t = 300ms) s Coils/Inductive Loads of 80Ω or Higher) (T _J Initial = +85°C)		ELD1	60	V
Inductive Switching Transient 1, Drain-to-Source (Waveform: R _{SOURCE} = 10Ω , t = $2.0ms$) (For Relay's Coils/Inductive Loads of 80Ω or Highe	ELD2	100	V		
Inductive Switching Transient 2, Drain-to-Source (Waveform: R _{SOURCE} = 4.0Ω , t = 50μ s) (For Relay's Coils/Inductive Loads of 80Ω or Highe	r) (T」Initia	ELD3	300	V	
Reverse Battery, 10 Minutes (Drain-to-Source) (For Relay's Coils/Inductive Loads of 80Ω or more)			Rev-Bat	-14	V
Dual Voltage Jump Start, 10 Minutes (Drain-to-Sou	ırce)		Dual-Volt	28	V
ESD Human Body Model (HBM)			ESD	4,000	V

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	820	mW
Thermal Resistance, Junction to Ambient (Note 5) Steady State		R _{0JA}	154	°C/W
Total Power Dissipation (Note 6)	PD	1,090	mW	
Thermal Resistance, Junction to Ambient (Note 6) Steady State		Reja	116	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

Notes:

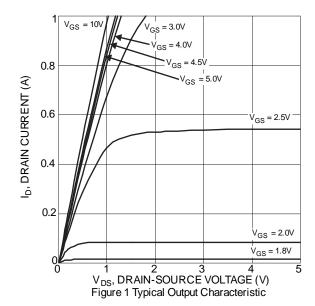
^{5.} Device mounted on FR-4 PCB, with minimum recommended pad layout.6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.

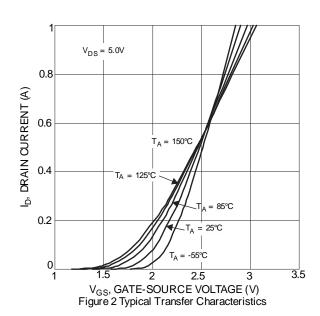


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

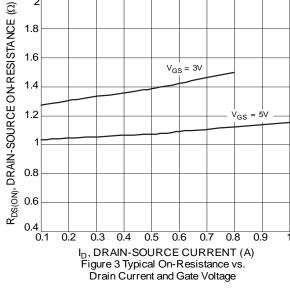
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 7)										
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 10mA$				
Zero Gate Voltage Drain Current	IDSS		_	50 0.5	μΑ	V _{DS} = 60V, V _{GS} = 0V V _{DS} = 12V, V _{GS} = 0V				
Gate-Source Leakage	Igss	_	_	±90 ±60	μA	V _{GS} = ±5V, V _{DS} = 0V V _{GS} = ±3V, V _{DS} = 0V				
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)									
Gate Threshold Voltage	VGS(TH)	1.3		2.0	V	V _{DS} = V _{GS} , I _D = 1mA				
Static Drain-Source On-Resistance	D		1.1	1.8	Ω	$V_{GS} = 5V, I_{D} = 0.15A$				
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	1.4	2.4	12	$V_{GS} = 3V, I_{D} = 0.15A$				
Forward Transfer Admittance	Y _{fs}	80	_	_	ms	V _{DS} = 12V, I _D = 0.15A				
Diode Forward Voltage	VsD		0.8	1.2	V	V _G S = 0V, I _S = 0.15A				
DYNAMIC CHARACTERISTICS (Note 8)										
Input Capacitance	C _{iss}		12.9	_	pF					
Output Capacitance	Coss		17	_	pF	V _{DS} = 12V, V _{GS} = 0V f = 1.0MHz				
Reverse Transfer Capacitance	Crss		0.84	_	pF	1 – 1.000112				
Total Gate Charge	Qg		0.74	_	nC	., -,,,				
Gate-Source Charge	Q_{gs}		0.19	_	nC	$V_{GS} = 5V, V_{DS} = 12V,$ $I_{D} = 150 \text{mA}$				
Gate-Drain Charge	Qgd	_	0.16	_	nC	ID = 150MA				
Turn-On Delay Time	tD(ON)		131	_	ns					
Turn-On Rise Time	t _R	_	301	_	ns	\/ 40\/ \/ 5\/				
Turn-Off Delay Time	tD(OFF)		582	_	ns	$V_{DD} = 12V$, $V_{GS} = 5V$				
Turn-Off Fall Time	tF	_	440	_	ns					

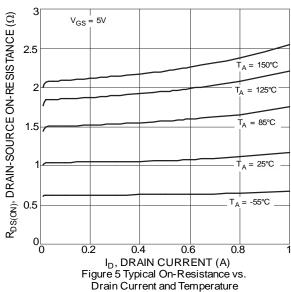
7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing. Notes:

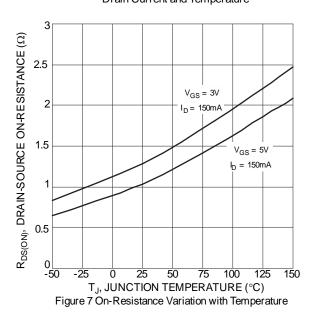


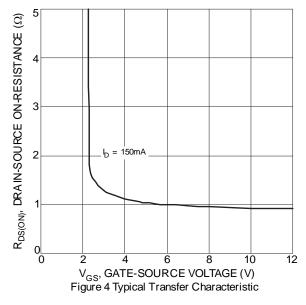


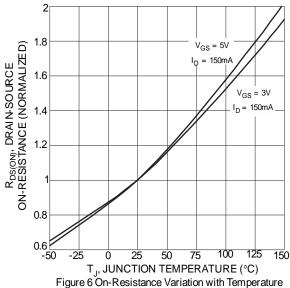












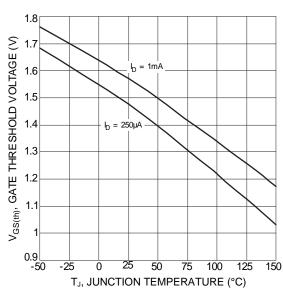
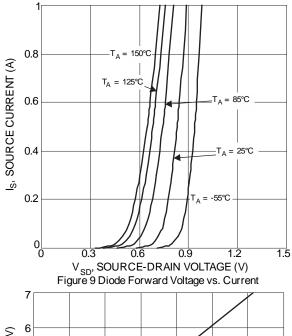
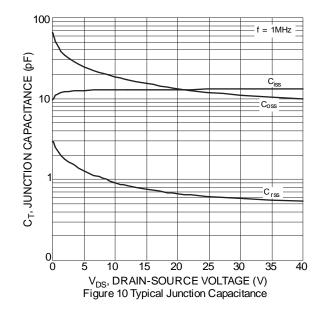
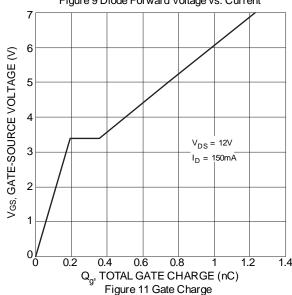


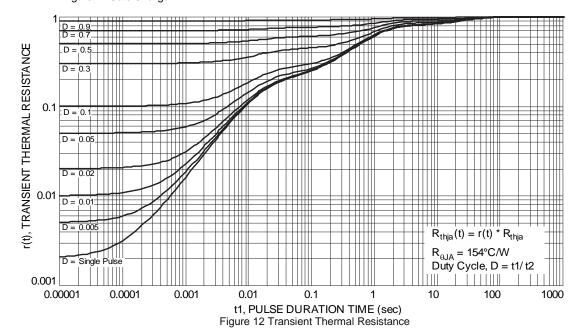
Figure 8 Gate Threshold Variation vs. Junction Temperature









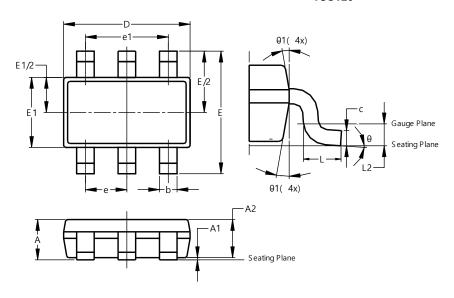




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

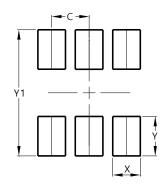


TSOT26							
Dim	Min	Тур					
Α	-	1.00	-				
A1	0.010	0.100	-				
A2	0.840	0.900	-				
D	2.800	3.000	2.900				
Е	2	.800 BS	С				
E1	1.500	1.700	1.600				
b	0.300	0.450	-				
С	0.120	0.200	-				
е	0.950 BSC						
e1	1	.900 BS	С				
L	0.30	0.50	-				
L2	0.250 BSC						
θ	0°	8°	4°				
θ1	4°	12°	-				
Α	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3 200



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